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- **EPIC™** (Enhanced-Performance Implanted **CMOS) Submicron Process**
- Typical V_{OLP} (Output Ground Bounce) $< 0.8 \text{ V at V}_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Typical V_{OHV} (Output V_{OH} Undershoot) $> 2 \text{ V at V}_{CC} = 3.3 \text{ V}, T_{A} = 25^{\circ}\text{C}$
- **Power Off Disables Outputs, Permitting** Live Insertion
- Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})
- **ESD Protection Exceeds 2000 V Per** MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- **Package Options Include Plastic** Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) WWW.DZSC.COM **Packages**

DB, DW, OR PW PACKAGE (TOP VIEW)

	Н		U		L.	
OE1	Ц	1	_	24	Ц	Vcc
A1		2		23		Y1
A2		3		22	0	Y2
A3		4		21		Y3
A4		5		20	0	Y4
A5		6		19		Y5
A6		7		18		Y6
A7		8		17	1	Y7
A8		9		16	0	Y8
A9		10		15	1	Y9
A10		11		14		Y10
GND	9	12		13		OE2

description

This 10-bit buffer/bus driver is designed for 1.65-V to 3.6-V V_{CC} operation.

The SN74LVC827A provides a high-performance bus interface for wide data paths or buses carrying parity.

The 3-state control gate is a 2-input AND gate with active-low inputs so that if either output-enable (OE1 or OE2) input is high, all ten outputs are in the high-impedance state. The SN74LVC827A provides true data at its outputs.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

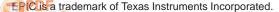
To ensure the high-impedance state during power up or power down, $\overline{\sf OE}$ should be tied to ${\sf V_{CC}}$ through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC827A is characterized for operation from -40°C to 85°C.

FUNCTION TABLE

		INPUTS	OUTPUT								
	OE1	OE2	Α	Υ							
	L	L	L	L							
	L	L	Н	Н							
	H	X	X	Z							
١	X	Н	Χ	Z							

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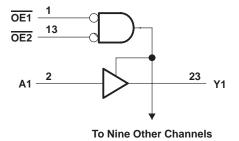


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logic symbol†

1 OE1 ΕN 13 OE2 23 **Y1 A1** 3 22 A2 **Y2** 4 21 **Y3 A3** 5 20 Α4 **Y4** 6 19 Y5 Α5 7 18 A6 **Y6** 8 17 **Y7** Α7 9 16 **Y8 A8** 10 15 **A9 Y9** 11 14 A10 Y10

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V _{CC}	–0.5 V to 6.5 V
Input voltage range, V _I (see Note 1)	0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V _O	
(see Note 1)	–0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, VO	
(see Notes 1 and 2)	–0.5 V to V _{CC} + 0.5 V
Input clamp current, I _{IK} (V _I < 0)	
Output clamp current, I _{OK} (V _O < 0)	
Continuous output current, I _O	±50 mA
Continuous current through V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3): DB package	
DW package	
PW package	120°C/W
Storage temperature range, T _{stq}	–65°C to 150°C

[‡] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The value of V_{CC} is provided in the recommended operating conditions table.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V-00	Supply voltage	Operating	1.65	3.6	V
VCC	Supply voltage	1.5		V	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$ 0.65 × V			
VIН	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V
VIH F	$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$				
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}	
VIL	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8	
٧ _I	Input voltage	•	0	5.5	V
\/-	Output valtage	High or low state	0	Vcc	V
VO.	Output voltage	3 state	0	5.5	V
		V _{CC} = 1.65 V		-4	
	Lligh lovel output output	$V_{CC} = 2.3 \text{ V}$		-8	
ЮН	High-level output current $V_{CC} = 2.7 \text{ V}$		-12	mA	
V _{IL} I		V _{CC} = 3 V		-24	
		V _{CC} = 1.65 V		4	
	Level book outside comment	V _{CC} = 2.3 V	8		1
IOL	Low-level output current	V _{CC} = 2.7 V		12	mA
	V _{CC} = 3 V			24	
Δt/Δν	Input transition rise or fall rate		0	10	ns/V
T _A	Operating free-air temperature		-40	85	°C

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

SN74LVC827A **10-BIT BUFFER/DRIVER** WITH 3-STATE OUTPUTS

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CO	ONDITIONS	v _{CC}	MIN	TYP [†]	MAX	UNIT	
	I _{OH} = -100 μA	1.65 V to 3.6 V	V _{CC} -0.2					
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2					
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	I _{OH} = -8 mA	2.3 V	1.7			٧		
VOH	Ιου - 12 mΛ		2.7 V	2.2			v	
	I _{OH} = -12 mA		3 V	2.4				
	$I_{OH} = -24 \text{ mA}$		3 V	2.2				
	I _{OL} = 100 μA		1.65 V to 3.6 V			0.2		
	I _{OL} = 4 mA	1.65 V			0.45			
VOL	I _{OL} = 8 mA	2.3 V			0.7	٧		
	I _{OL} = 12 mA	2.7 V			0.4			
	I _{OL} = 24 mA		3 V			0.55		
lį	V _I = 0 to 5.5 V		3.6 V			±5	μΑ	
l _{off}	V _I or V _O = 5.5 V		0			±10	μΑ	
loz	V _O = 0 to 5.5 V		3.6 V			±10	μΑ	
	$V_I = V_{CC}$ or GND		0.01/			10	μА	
Icc	$3.6 \text{ V} \leq \text{V}_{\text{I}} \leq 5.5 \text{ V}^{\ddagger}$	IO = 0	3.6 V			10		
ΔlCC	One input at V _{CC} – 0.6 V,	Other inputs at V _{CC} or GND	2.7 V to 3.6 V			500	μΑ	
Control inputs	V. Vaaar CND		0.01/		5		pF	
C _i Data inputs	V _I = V _{CC} or GND		3.3 V		4	4		
Co	$V_O = V_{CC}$ or GND		3.3 V		7		pF	

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$. ‡ This applies in the disabled state only.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = ± 0.1	1.8 V 5 V	V _{CC} =	2.5 V 2 V	V _{CC} = 2.7 V		V _{CC} = 3.3 V ± 0.3 V		UNIT
	(INFOT)	(001F01)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	А	Υ	§	§	§	§		7.1	1	6.7	ns
t _{en}	ŌĒ	Υ	§	§	§	§		8.5	1	7.3	ns
tdis	ŌĒ	Y	§	§	§	§		7.3	1.8	6.7	ns
t _{sk(o)} ¶										1	ns

[§] This information was not available at the time of publication.

operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V _{CC} = 1.8 V ± 0.15 V	V _{CC} = 2.5 V ± 0.2 V	V _{CC} = 3.3 V ± 0.3 V	UNIT	
			CONDITIONS	TYP	TYP	TYP		
Card	Power dissipation capacitance	Outputs enabled	f = 10 MHz	§	§	24	nE	
C _{pd} pe	per buffer/driver	Outputs disabled f = 10 MHz	§	§	5	pF		

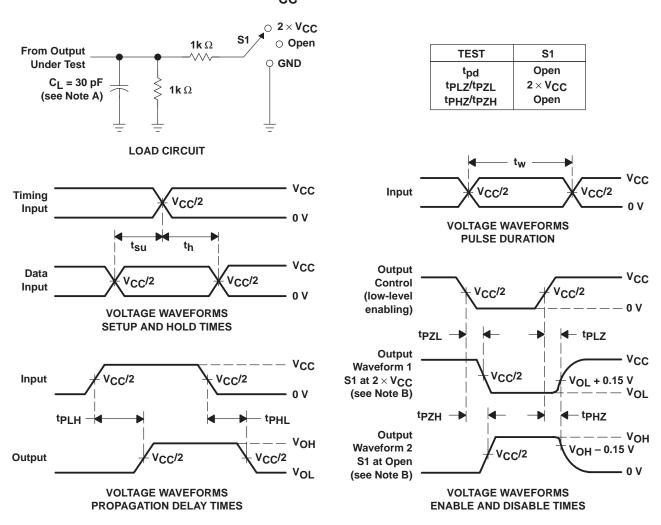
[§] This information was not available at the time of publication.



 $[\]P$ Skew between any two outputs of the same package switching in the same direction

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PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$



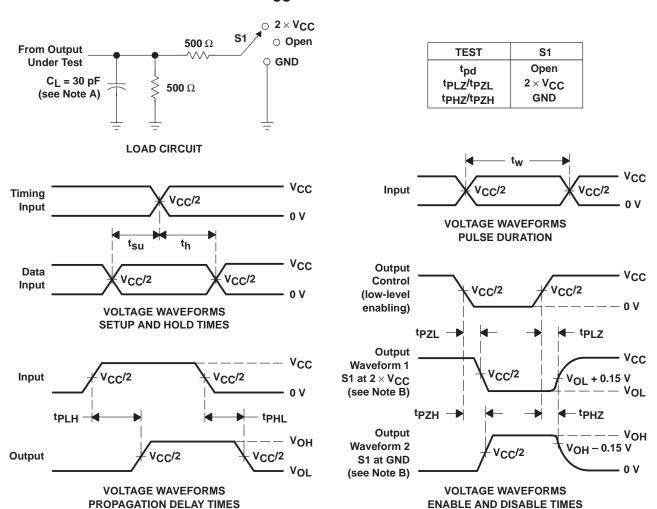
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$

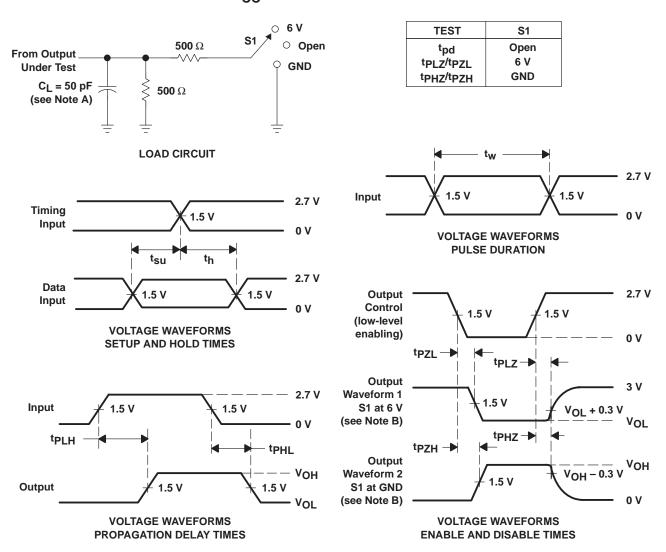


- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , $t_f \leq$ 2 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLz and tpHz are the same as tdis.
 - F. t_{PZL} and t_{PZH} are the same as t_{en}.
 - G. tpLH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms



PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , $t_r \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms



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